ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748–5089

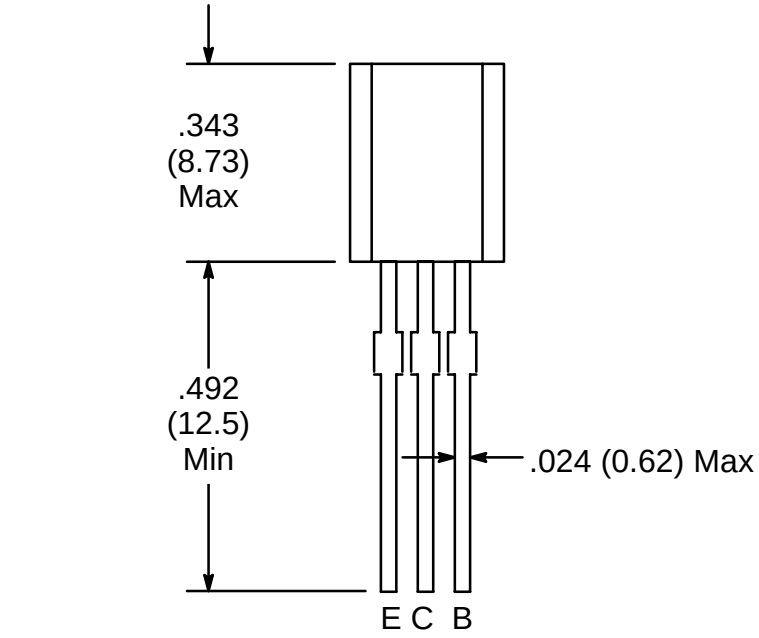
NTE382 (NPN) & NTE383 (PNP)
Silicon Complementary Transistors
Audio Frequency Driver

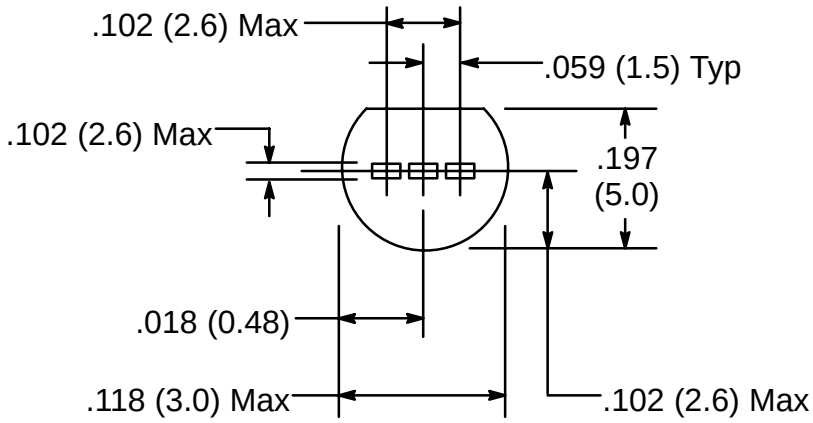
Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

Collector–Base Voltage, V_{CBO} 120V
Collector–Emitter Voltage, V_{CEO} 100V
Emitter–Base Voltage, V_{EBO} 5V
Collector Current, I_C
  Continuous 1A
  Peak 2A
Collector Power Dissipation, P_C 900mW
Operating Junction Temperature, T_J . . . . . +150°C
Storage Temperature Range, T_{stg} . . . . . –55° to +150°C

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector–Base Breakdown Voltage	$V_{(BR)CBO}$	I_C = 10μA, I_E = 0	120	–	–	V
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = 1mA, R_{BE} = ∞	100	–	–	V
Emitter–Base Breakdown Voltage	$V_{(BR)EBO}$	I_E = 10μA, I_C = 0	5	–	–	V
Collector Cutoff Current	I_{CBO}	V_{CB} = 100V, I_E = 0	–	–	10	μA
DC Current Gain	h_{FE}	V_{CE} = 5V, I_C = 150mA	160	–	320	
		V_{CE} = 5V, I_C = 500mA	30	–	–	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 500mA, I_B = 50mA	–	–	1.0	V
Base–Emitter Voltage	V_{BE}	V_{CE} = 5V, I_C = 150mA	–	–	1.5	V
Current Gain–Bandwidth Product	f_T	V_{CE} = 5V, I_C = 150mA	–	140	–	MHz
Capacitance	C_{ob}	V_{CB} = 10V, I_E = 0, f = 1MHz	–	20	–	pF





.236 (6.0)Dia Max

.102 (2.6) Max